

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

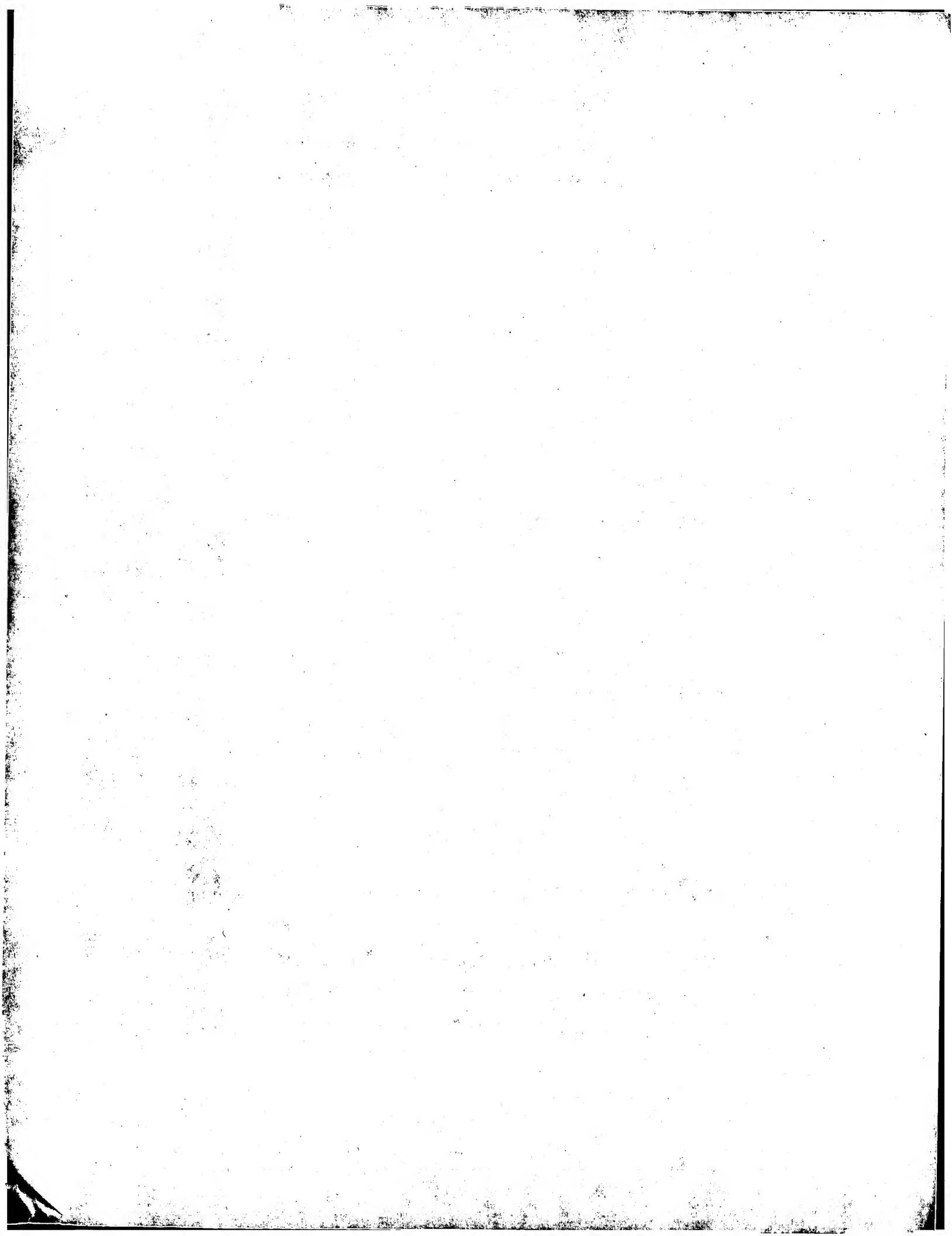
Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**



(19) World Intellectual Property Organization
International Bureau(43) International Publication Date
7 February 2002 (07.02.2002)

PCT

(10) International Publication Number
WO 02/11176 A1(51) International Patent Classification⁷:**H01J 37/34**

(21) International Application Number:

PCT/GB01/03229

(22) International Filing Date:

18 July 2001 (18.07.2001)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

0018391.3 27 July 2000 (27.07.2000) GB
0021754.7 5 September 2000 (05.09.2000) GB(71) Applicant (for all designated States except US): **TRIKON HOLDINGS LIMITED [GB/GB]**; Coed Rhedyn, Ringland Way, Newport, Gwent NP6 2TA (GB).

(71) Applicant and

(72) Inventor: **BURGESSION, Stephen, Robert [GB/GB]**; 39 Clydach Avenue, Rassau, Ebbw Vale, Gwent NP23 5TJ (GB).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **GOERGENS, Carsten [DE/DE]**; Weinbergstrasse 50, 01129 Dresden (DE).

(54) Title: MAGNETRON SPUTTERING

(74) Agents: **DUNLOP, Brian, Kenneth, Charles et al.; Wynne-Jones, Laine & James, 22 Rodney Road, Cheltenham, Gloucestershire GL50 1JJ (GB).**

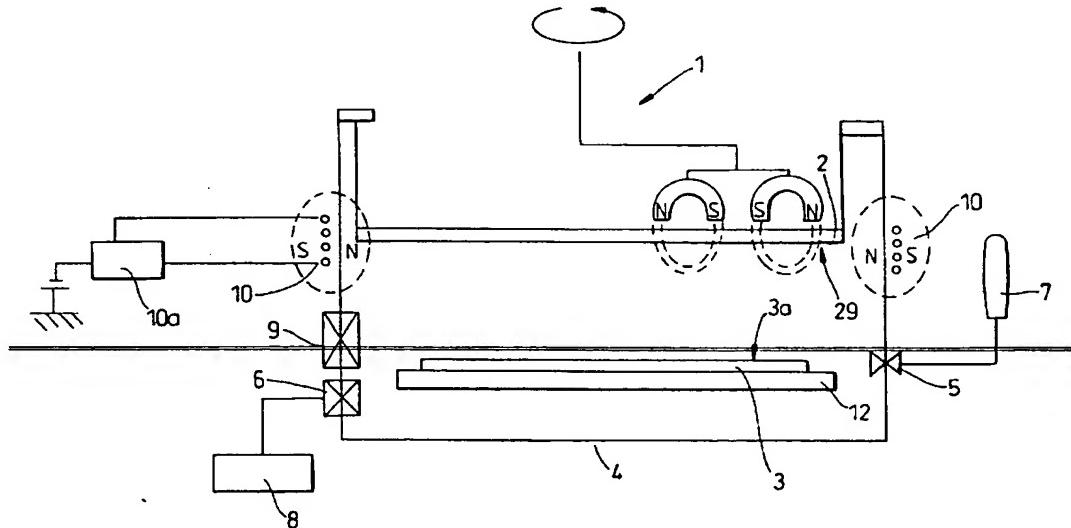
(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.



(57) Abstract: A magnetron sputtering apparatus has a controller (10a) or selectively releasing the spread of plasma on a substrate (3) on a support (12). The controller can also contain the plasma when the substrate is to be coated with the target material. This enables cleaning of the target surface during intervals between deposition of target material onto a desired substrate, such as a wafer, and ensures that layers or flakes of back-scattered deposited target material do not build up on the target itself. A platen coil is located between the magnetron and the support to increase both uniformity and density of target material arriving nearly normal to the substrate surface.

WO 02/11176 A1

MAGNETRON SPUTTERING

This invention relates to apparatus and methods for
5 magnetron sputtering.

In US Patent No. 5,593,551 issued to Lai, the disclosure of which is incorporated herein by reference, there is described an apparatus and method for magnetron sputtering in which a first closed-loop magnet means is positioned adjacent to a dish-shaped sputter target back surface for creating a closed-loop magnetic tunnel to the front surface of the sputter target, the magnet means being in the form of a plurality of magnets surrounding a central axis of a dish-shaped sputter target for containing and guiding a plasma relative to a substrate. The improvement is a second closed-loop magnet means positioned around the sputter target perimeter and being comprised of a number of bucking magnets, which may be permanent magnets or electro magnets, which collectively provide a fixed field around the sputter target to thereby reduce or inhibit the spreading of the discharge track of the plasma beyond the edge of the target as the operating pressure of the sputtering system is reduced.

The second closed-loop magnet means solves the problem in
25 that the voltage at which a magnetron operates is primarily

a function of the ease of ionisation. It is, in turn, a function of the gas, its pressure, the applied voltage, the strength of the magnetic field and the ionisation losses from the plasma. As pressure is dropped so operating voltages rise until practical limits are reached e.g. the power supply or electrical connections to the target.

Extremely high voltages are undesirable as they cause the plasma to emit higher energy electromagnetic waves that are potentially dangerous. Therefore, work has concentrated upon reduction of losses from the plasma by e.g. operating the plasma in an enclosed area bounded by a bucking arrangement, as in the '551 patent. This allows magnetron operation at pressures of 0.1mT to 1mT. This low pressure operation is beneficial as a means of improving step coverage.

However, the design of this system and method of sputtering has the disadvantage that due to the confinement of the primary magnetic field by the secondary magnetic field, there is little or zero erosion of the target material around the periphery of the target. As a consequence, the periphery thereof can thereafter be contaminated by back scattered deposits of eroded material, such as atoms or molecules. This re-deposited material generally does not adhere well to the otherwise clean periphery of the target

and can thereafter flake off to contaminate the substrate to which a thin film of the material is being applied or is to be applied.

The present invention is derived from the realisation that by replacing the permanent bucking arrangement of the prior art, which essentially provides a fixed magnetic field normal to the erosion region, with controllable DC coils located adjacent but outside of the periphery of the target assembly, it is then possible to vary the magnetic field, through the use of suitable switching and control circuits, to mitigate the foregoing disadvantages and to "clean" the whole of the target surface before a new thin film process is begun.

According to a first aspect of the invention there is provided a magnetron sputtering apparatus including:

a target;

a magnetron assembly for the target arranged to produce uniform erosion of the target across its surface, and

a support for holding a substrate on to which a film of target material is to be deposited from the target, characterised in that the apparatus further includes:

a closed loop magnet assembly located around the sputter target perimeter for magnetically containing or

restricting a plasma formed adjacent to the target surface to alter the erosion pattern of the target, and

5 a control for selectively releasing the spread of the plasma over substantially the entire surface of the target such that the surface thereof may be eroded and selectively containing the plasma within the periphery of the target.

Prior art magnetron devices have been developed to provide good uniform erosion of the target but embodiments of the present invention allow preferential erosion during 10 deposition whilst further allowing the apparatus to operate in the normal mode for cleaning. With this arrangement, sputtering apparatus according to the invention enables cleaning of the target surface during intervals between deposition of target material onto a desired substrate, 15 such as a wafer. This ensures that layers or flakes of back scattered deposited target material do not build up on the target itself to thereafter e.g. flake off and contaminate the wafer.

According to a second aspect of the invention there is 20 provided a method of magnetron sputtering a target by using apparatus in accordance with the first aspect of the invention, which method includes the steps of selectively varying or eliminating the magnetic field provided by the coils to allow thereby the plasma to erode the entire

surface of the target material when a substrate material to be coated is not being exposed to the sputtered particles, to thereby prevent build up of unwanted layers or flakes of the target material around the periphery thereof.

5 According to another aspect, the invention provides a method of sputter deposition on a substrate without collimation filter including, during sputter deposition, restricting the plasma to a central area of a target by means of a circumjacent coil, and

10 applying a magnetic containment field around a space located above a support for a substrate to be sputtered.

According to a further aspect there is provided a method of controlling a magnetron sputtering assembly having a target having a sputter surface, the magnet of the magnetron 15 assembly being moveable with respect to the target and having a plasma generator and a plasma containment arrangement including operating the plasma containment arrangement in a first, cleaning, mode wherein the plasma extends across substantially the whole sputter surface and 20 a second, deposition mode, when the plasma is contained within the periphery of the sputter surface, and

applying a magnetic containment field around a space located above the support for a substrate to be sputtered.

The inventors have noted that the ability to confine the plasma adjacent a restricted area of target, reduces the angular distribution of the sputter material and, particularly in long throw chambers, can remove the need 5 for collimators even with high aspect ratio holes.

The invention will now be described, by way of example only, with reference to the accompanying drawings in which: Figure 1 is a schematic view shown in part cross section of the inside of a sputtering chamber incorporating the 10 apparatus of the invention;

Figure 2 is a schematic cross-sectional view showing a selected portion of target material of the apparatus of Figure 1 partially eroded by plasma contained by the second magnet means;

15 Figure 3 is a view corresponding to that of Figure 2 but in which the whole of the surface of one side of the target material has been eroded;

Figure 4 is a schematic view of an alternative set-up including a further magnetic assembly;

20 Figures 5(a) and (b) are electron micrographs of the centre and edge respectively of a wafer treated in accordance with Experiment 1;

Figures 6(a) and (b) are corresponding micrographs for Experiment 2;

Figures 7(a) and (b) are corresponding micrographs for the first set-up in Experiment 3;

Figure 8 is a plot of base coverage against gas pressure with the target coil on;

5 Figure 9 is a similar plot to Figure 8 with the target coil off; and

Figures 10 and 11 are further such plots for different bias conditions at the centre and edge respectively.

Referring firstly to Figure 1, there is shown a rotatable
10 magnetron assembly shown generally at 1 comprising a closed loop array of magnets which is used to generate a magnetic field in the volume between the front surface 2a of a target 2, which may typically be titanium and an upper surface 3a of a substrate 3, typically a semi-conducting or
15 insulating wafer.

The target 2 and substrate 3 are each contained within a vacuum low pressure vessel in the form of a chamber 4 through which a stream of noble gas such as argon may pass at low pressure via an inlet valve 5 and an outlet valve 6
20 from a respective gas source reservoir 7 and a vacuum pump 8, typically a cryogenic pump.

An access door 9 is shown schematically in a side wall of the chamber 4, in order to allow access to the interior of the chamber and in particular for removing at regular

intervals a substrate 3 onto which a thin film of the material from the target 2 has condensed following sputtering of the latter via ionic bombardment, in a conventional manner.

5 Continuously wound DC coils 10 surround the magnetron assembly 1 and lie essentially coplanar with the major plane of the target 2. As will be appreciated, the DC coils 10 can effectively act as a solenoid when excited by a DC current to thereby generate an additional magnetic field, shown in dotted outline, surrounding the magnetron assembly 1 to thereby, when so excited, constitute a bucking arrangement of inwardly facing identical poles.

A control 10a is provided for selective varying the strength of the magnetic field produced by the coils 10 by 10 selectively varying suitable switching and associated software within the control 10, in contrast to the essentially fixed field arrangement shown in the '551 patent. This has a significant advantage in that, prior to the introduction of a substrate into the chamber 3, 15 excitation of the DC coils 10 can be varied to create a wider containment of the surrounding the plasma such that the whole of the lower surface 2a of the target 2 may be sputter etched and thereby cleaned, whereafter the substrate 3 can be introduced into the chamber, the door 9

closed and a smaller containment "bucket" used to contain the plasma by a suitable adjustment to the power supplied to the DC coils 10.

The field intensity produced by the coils 10 may be varied
5 or eliminate altogether, by simply reducing the current thereto in the interval between thin film deposition on a desired substrate 3. This may be demonstrated with reference to Figures 2 and 3, with Figure 2 showing the etching pattern of the target 2 when the DC coils 10 are maintained in a state to contain closely the plasma, e.g.
10 when they are producing their maximum magnetic field. It will be seen that, an annular perimeter 2b comprised of a layer of re-deposited target material in the form of flakes may therefore build up, as in the apparatus described with
15 reference to the '551 patent.

In contrast, and as can be seen in Figure 3, by varying the magnetic field generated by the DC coils 10 to allow for the whole of the surface 2a of the target to become exposed to ionic bombardment, the whole of the surface may
20 therefore be cleaned.

Variation of the magnetic field by the DC coils 10 may also be achieved by reversing the current flow, thereby providing a reversed field.

The cleaning made possible by the present invention is preferably performed at a higher pressure, typically of 1mT to 10mT since there are problems with operating the magnetron at low pressure, for the reasons set out in the 5 preamble hereto.

An example of the advantage of the apparatus and method of the invention is found where titanium and titanium nitride is required to be deposited on a substrate as a barrier layer. Economically, it is advantageous to deposit both 10 the titanium and the titanium nitride in the same process chamber and a common practice is to deposit the titanium by sputtering in an inert ambient atmosphere, such as, in argon, and for the titanium nitride in a reactive ambient atmosphere, including nitrogen. This technique requires 15 the target to be cleaned after every titanium nitride deposition in order to remove nitrogen contamination from the surface. Using the apparatus and method of the invention there is therefore a very convenient opportunity to clean, additionally, the edge of the target by reducing, 20 removing or reversing the magnetic field generated by the external DC coils 10. A typical sequence would consist of the steps of:

(1) Depositing titanium at low pressure under a high magnetic "bucking" field generated by the external DC coils 10.

5 (2) when depositing titanium nitride using a high magnetic field again generated by the external DC coils 10, and

(3) after removing the substrate, or shielding it from further deposition by use of a shutter, which may also act as a collector for the sputter-cleaned target material, removing, reducing or reversing the field created by the DC 10 coils 10 to thereafter clean the whole of the target surface.

It will, however, be understood that the same sequence described above can be used to deposit these or other metal/metal nitride combinations without departing from the 15 spirit or scope of the invention.

The above results show that the 'target' coil improves base coverage results and it has also been discovered that this can be improved further by the addition of another coil as shown in Figure 4. This additional platen coil 11 is 20 located between the target and the wafer, but below the 'target' coil.

Before discussing this arrangement in detail, it may be helpful to provide some background explanation. Sputtering so-called 'step coverage' is better than thermal

evaporation because of the higher energy level of the arriving material and the possibility of large area sources close to the substrate giving rise to a wide angular distribution of arriving target material. Heating the 5 substrate increases this further. Ideally a conformal surface covering is desired, but the holes present a problem as all material to coat the insides and base must pass through their mouths.

For barrier deposition the only surfaces of interest are 10 within the holes. Ideally none would arrive on the field (an impossibility). For contact barriers, as the contact is at the base of the hole, only the base of the hole requires coating and as contact holes get smaller and aspect ratios increase ideally only the base would be 15 coated, leaving a larger volume of the hole for the principal conductor material having a lower resistance than the barrier material.

So techniques to increase the directionality of the sputtering are employed which attempt to have sputtered 20 material with a flight path normal to the substrate surface thus improving the probability of material deposition at the base of high aspect ratio contact holes.

Two principal techniques are employed: ionisation and collimation. These are not mutually exclusive and

ionisation of the sputtered material has been used in combination with 'collimating filters' (being high aspect ratio holes through which sputtered material must pass before arriving at the substrate) and collimation whereby 5 the source to substrate distance is increased e.g. to about 250mm or about 500mm (c.f. approximately 25mm for normal magnetron sputtering). This increased distance allows low angle sputtered material to be lost to the side walls, with only that material arriving approximate normal to the 10 substrate surface to arrive thus increasing the proportion of material deposited at the bottom of holes (which are, in essence, collimation filters themselves).

In the present invention, it could be said that collimation is being achieved, without using an actual collimator, by 15 controlling the source of the sputtered material. The 'target' coil confines the plasma and thus reduces the angular distribution of sputtered material. One surprising result from the experiments shown below is that optical spectroscopy suggests that metal ionisation takes place and 20 thus this arrangement achieves much of that using ionising coils but without the ionising coil. In any event base coverage using this system is significantly affected by the bias voltage on the support.

A further set of experiments investigated the influence of additional electromagnetic coils on the hole base coverage of sputtered titanium films in a 'long throw' magnetron sputter chamber arrangement with an approximate 240mm
5 source to substrate spacing. 'Long throw' generally indicates a source substrate separation of over about 200 mm.

The set up is indicated in Figure 4. One set of coils ("target coils") 10 was positioned around the target and
10 upper part of the sputter chamber as shown schematically in Figure 1. The polarity of the coil current was set to induce a magnetic field with the same direction as the outer pole of the magnetron ("stronger outer poles"). This allows the system to operate at low working gas pressures
15 by confining the plasma at the edge of the target, lowering the plasma impedance.

Additionally, a second set of electromagnetic coils ("platen coils") 11 was positioned around the lower part of the sputter chamber, close to the support 3. The two sets
20 of coils were operated independently using different power supplies. Experiments were run with the coils energised to present different magnetic poles into the sputtering chamber. In general significantly better base coverage was achieved when both the target and platen coil magnetic

polarity was opposed to the outer pole of the target magnetron (in a 'bucking' configuration) as shown in experiment 3. So, for the sake of clarity, if the magnetron presented a North pole to its outer periphery, 5 then the coils were generally energised so as to present a North pole on their inner surface. Reversing the magnetic field of the platen coil(s) 11, see experiment 4, (such that they present an opposing magnetic field to the outer field of the magnetron) was found to improve symmetry of 10 base coverage across the wafer; however base coverage thickness was reduced.

Cathode power, sputter gas pressure and deposition temperature were kept constant, whilst the platen bias power and coil currents were varied. The film properties 15 investigated are base coverage (at the centre and edge of the wafer) and the asymmetry of the base coverage (across on wafer and within one contact hole).

1. Experimental Process Parameters:

20 Target Power: 30kW
Ar Gas flow: 100sccm
Pressure: 2.5 mTorr
Platen Temp.: 200°C

25 Size of contact hole: 2.5µm, aspect ratio: 2.7:1

2. Results and Conclusions

Experiment 1.

	Target Coil Current =	OA
	Platen Coil Current =	OA
	Platen bias voltage =	-105V
5	Sputtering efficiency =	77 Å kW ⁻¹ min ⁻¹
	Base coverage centre =	26%
	Base coverage edge, average =	25%
	Asymmetry of base coverage across wafer (max-min)/(max+min) =	4%
10	Asymmetry of base coverage within one contact (max-min)/(max+min) =	4%

The base coverage achieved is shown in the electron micrographs shown in Figure 5.

15 Experiment 2

	Target Coil Current =	170A
	Platen Coil Current =	OA
	Platen bias voltage =	-105V
20	Sputtering efficiency =	45 Å kW ⁻¹ min ⁻¹
	Base coverage centre =	63%
	Base coverage edge, average =	51%
25	Asymmetry of base coverage across wafer (max-min)/(max+min) =	19%
	Asymmetry of base coverage within one contact (max-min)/(max+min) =	15%

30 The base coverage achieved is shown in the electron micrographs shown in Figure 6.

		Experiment
35		3 4
		Reversed
		Platen
		Mag field
	Target Coil Current =	170A
	Platen Coil Current =	40A
40	Platen bias voltage =	-90V
	Sputtering efficiency Å kW⁻¹ min⁻¹ =	41
	Base coverage centre =	70%
	Base coverage edge, average =	59%
	Asymmetry of base coverage across wafer (max-min)/(max+min) =	11%
45	Asymmetry of base coverage within one contact (max-min)/(max+min) =	5%
		1%

The base coverage achieved in experiment 3 is shown in the electron micrographs shown in Figure 7.

- 5 The reversed magnetic field experiment 4, in which only the field in the platen coils is reversed, is not entirely comparable. The system has power control for substrate bias, yet sputtering is voltage not current driven.
 10 Anything over 100V is likely to cause significant resputtering, perhaps resputtering material on the base of holes onto the sidewalls. (No micrographs for reverse magnetic field shown here).

		Experiment	
		5	6
15		Reversed	
	(d)	Platen	
	Target Coil Current =	Mag field	OA
	Platen Coil Current =		170A
20	Platen bias voltage =	-110V	-160V
	Sputtering efficiency Å kW ⁻¹ min ⁻¹ =	93	82
	Base coverage centre =	59%	23%
	Base coverage edge, average =	43%	19%
25	Asymmetry of base coverage across wafer (max-min)/(max+min) =	16%	5%
	Asymmetry of base coverage within one contact (max-min)/(max+min) =	1%	12%

30 Again these experiments and in particular the reversed magnetic field experiment is not entirely comparable. The system has power control for substrate bias, yet sputtering is voltage not current driven. Anything over -100V is likely to cause significant resputtering, perhaps resputtering material on the base of holes onto the sidewalls. No micrographs for this experiment shown here.
 35 Further experiments are required keeping bias to a =/-<-100v threshold.

When comparing Figure 5 and Figure 6, it is apparent that
 40 the addition of 'target coils' improves the base coverage of the sputtered films at the centre as well as at the edge of the wafer by more than 50%

A drawback, however is the 3 to 4-fold increase in asymmetry of the base coverage, across the wafer as well as within a contact hole. This increase in asymmetry can however be significantly reduced by addition of platen coils 11 (Figure 4). These 'platen' coils 11 increase both uniformity (reduced asymmetry) and density of target material arriving nearly normal to the substrate surface (increased hole base coverage). Reversing the magnetic pole of the platen coil further increases symmetry across the wafer but at a reduced base coverage.

It is also noted that sputtering efficiency falls when the 'target' magnetic coils are used. This is a measure of the average material thickness upon the wafer per target kilowatts of power per minute. It may be that confinement of target plasma (of comparable power) to a smaller area increases plasma density sufficiently to significantly increase ionisation of sputtered material, but at the cost of a reduced sputtering rate due to the reduction in target area erosion due to reduced area of target exposed to plasma. Thus less material is being sputtered, but at a higher energy level.

As has been mentioned before it is believed that metal ionisation is taking place as a result of this new configuration. Whilst it appears desirable to ionise an

amount of the sputter material, complete ionisation will not usually be appropriate.

The evidence for this is as follows:

This improvement in base coverage is gas pressure
5 insensitive. See attached Figures 8 and 9. Whilst turning the bias on at 1 millitorr has a similar percentile improvement in both cases, it is felt that the fact that the bias 'on' improvement is pressure insensitive shows that there is a significant degree of metal ionization.
10 This is extremely unusual for magnetrons that are generally considered to produce insignificant amount of metal ions, thus internal RF driven ionizing coils are usually required.

It would appear that by confining the plasma and applying
15 high levels of power to the magnetron at the 'right' pressure regime, metal ionisation is caused in the absence of a separate ionizing source. The addition of a further coil between the "target" coil and the substrate further improves base coverage and symmetry of base coverage across
20 a wafer. Whilst these have been identified as two discrete D.C. coil assemblies in this disclosure, they may be one assembly with varied winding densities to provide a graded magnetic field strength between the target area and the substrate area of the chamber. The experiments appear to

20

show that metal ionization occurs at high magnetron power levels only. At lower magnetron power levels, base coverage is poorer, see Figures 10 (center) and 11 (edge). These experiments were conducted with only the target coil energized. They show the influence on hole base coverage of wafer bias plotted against pressure at two different target power levels, 30kw and 8kw. As can be seen, at 5 30kws of target power, considered to be a 'high' power level wafer bias has a significant effect, whereas at 'low' target power bias has either no significant effect, the differences being considered to be within measurement 10 error.

The magnetron target considered throughout these experiments is of 330mm diameter, a conventional size for 15 200mm wafers and of conventional moving magnet design meaning that there is an erosion path adjacent the magnetic racetrack giving a non-uniform plasma density over the target surface.

20

CLAIMS

1. A magnetron sputtering apparatus including:
 - a target;
 - a magnetron assembly for the target arranged to produce uniform erosion of the target across its surface, and
 - a support for holding a substrate onto which a film of target material is to be deposited from the target, characterised in that the apparatus further includes:
 - 10 a closed loop magnet assembly located around the sputter target perimeter for magnetically containing or restricting a plasma formed adjacent to the target surface to alter the erosion pattern of the target, and
 - 15 a control for selectively releasing the spread of the plasma over substantially the entire surface of the target such that the surface thereof may be eroded and selectively containing the plasma within the periphery of the target.
2. Apparatus as claimed in Claim 1 further including a further magnetic assembly located to surround a space above the support.
- 20 3. Apparatus as claimed in Claim 1 or Claim 2 wherein the control selectively releases the spread of plasma when a substrate on the support is shielded therefrom or prior to a substrate being placed on the support and selects the

containing of the plasma when a substrate is to be coated with the target material.

4. Apparatus as claimed in any one of Claims 1 to 3 wherein the further magnetic assembly is of lower strength
5 than the moveable closed loop magnetic assembly.

5. Apparatus as claimed in any one of Claims 1 to 4 wherein the magnetic assemblies have separate controls.

6. Apparatus as claimed in any one of the preceding claims wherein one or both magnet assemblies are arranged
10 in a bucking configuration with respect to the target magnetron.

7. Apparatus as claimed in any one of the preceding claims, wherein the second magnetic assembly of the closed loop magnetic assembly is composed of DC electromagnetic
15 coils.

8. Apparatus as claimed in any one of the preceding claims, wherein the target periphery is located inside a vacuum chamber and the second magnetic assembly of the closed loop magnetic assembly is composed of coils external
20 to the vacuum chamber.

9. A method of controlling a magnetron sputtering assembly having a target having a sputter surface, the magnet of the magnetron assembly apparatus being moveable with respect to the target and having a plasma generator

and a plasma containment arrangement including the steps of: operating the plasma containment arrangement in a first, cleaning mode wherein the plasma extends across substantially the whole sputter surface and a second, 5 deposition mode, when the plasma is contained within the periphery of the sputter surface, and

applying a magnetic containment field around a space located above the support for a substrate to be sputtered.

10. A method as claimed in Claim 9 wherein the plasma containment arrangement is constituted by a plurality of DC electro-magnets arranged in a bucking configuration.

11. A method as claimed in Claim 9 or Claim 10 wherein a control selects the first mode prior to or in-between deposition steps and the second mode during deposition 15 steps.

12. A method of sputter deposition on a substrate without collimation filter including, during sputter deposition, restricting the plasma to a central area of a target by means of a circumjacent coil, and

20 applying a magnetic containment field around a space located above a support for a substrate to be sputtered.

13. A method as claimed in Claim 12 wherein the method is performed in a long throw chamber.

14. A method as claimed in Claim 12 or Claim 13 wherein a bias is applied to the substrate.

15. A method as claimed in Claim 14 performed in the absence of a separate ionising source.

5 16. A method as claimed in Claim 14 or Claim 15 wherein the sputtered material is at least partially ionised during the sputtering process.

17. A method as claimed in any one of Claims 12 to 16 wherein the plasma is allowed to extend over the central
10 area of the target for cleaning the target, when deposition is not taking place.

1/9

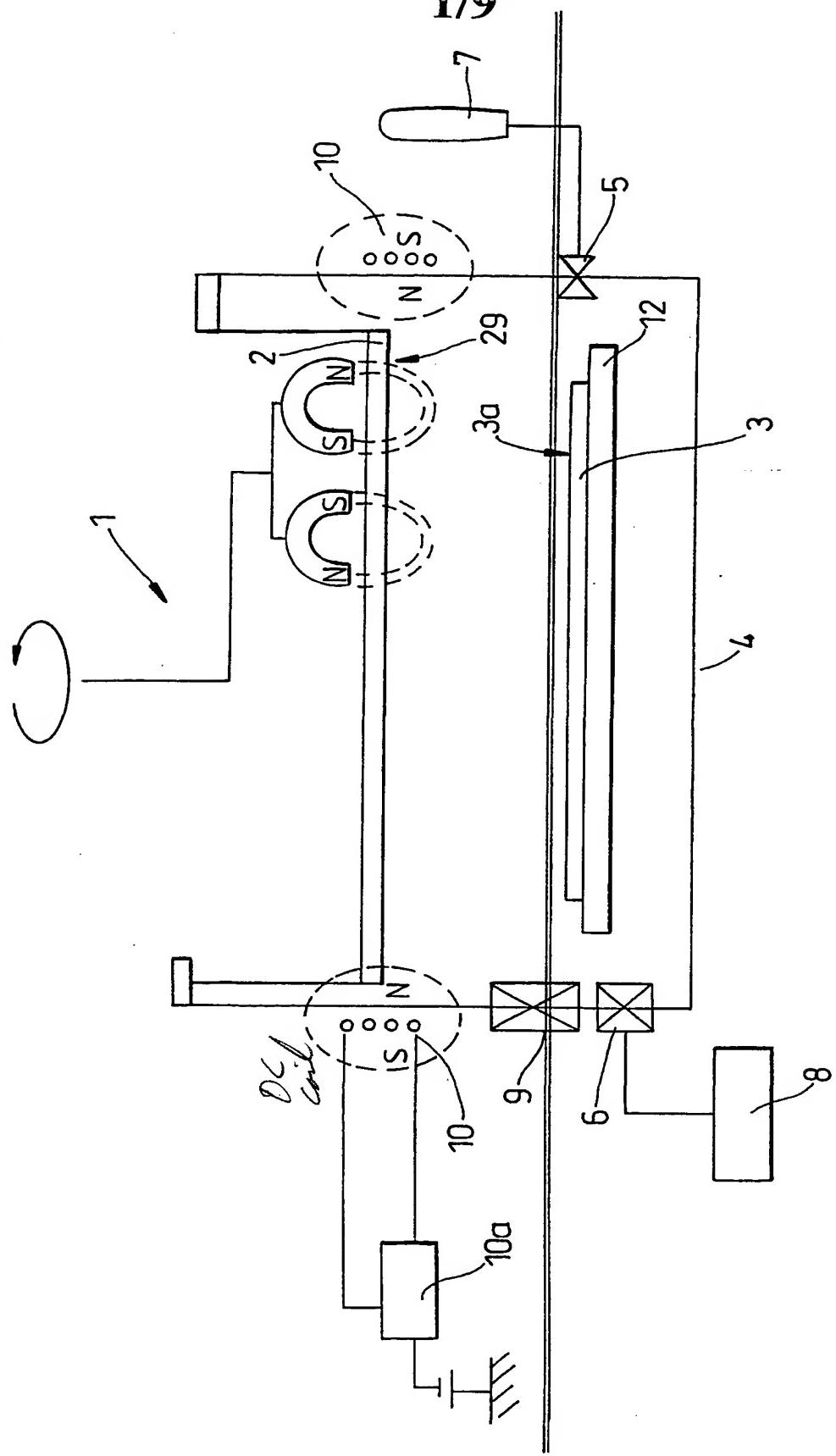
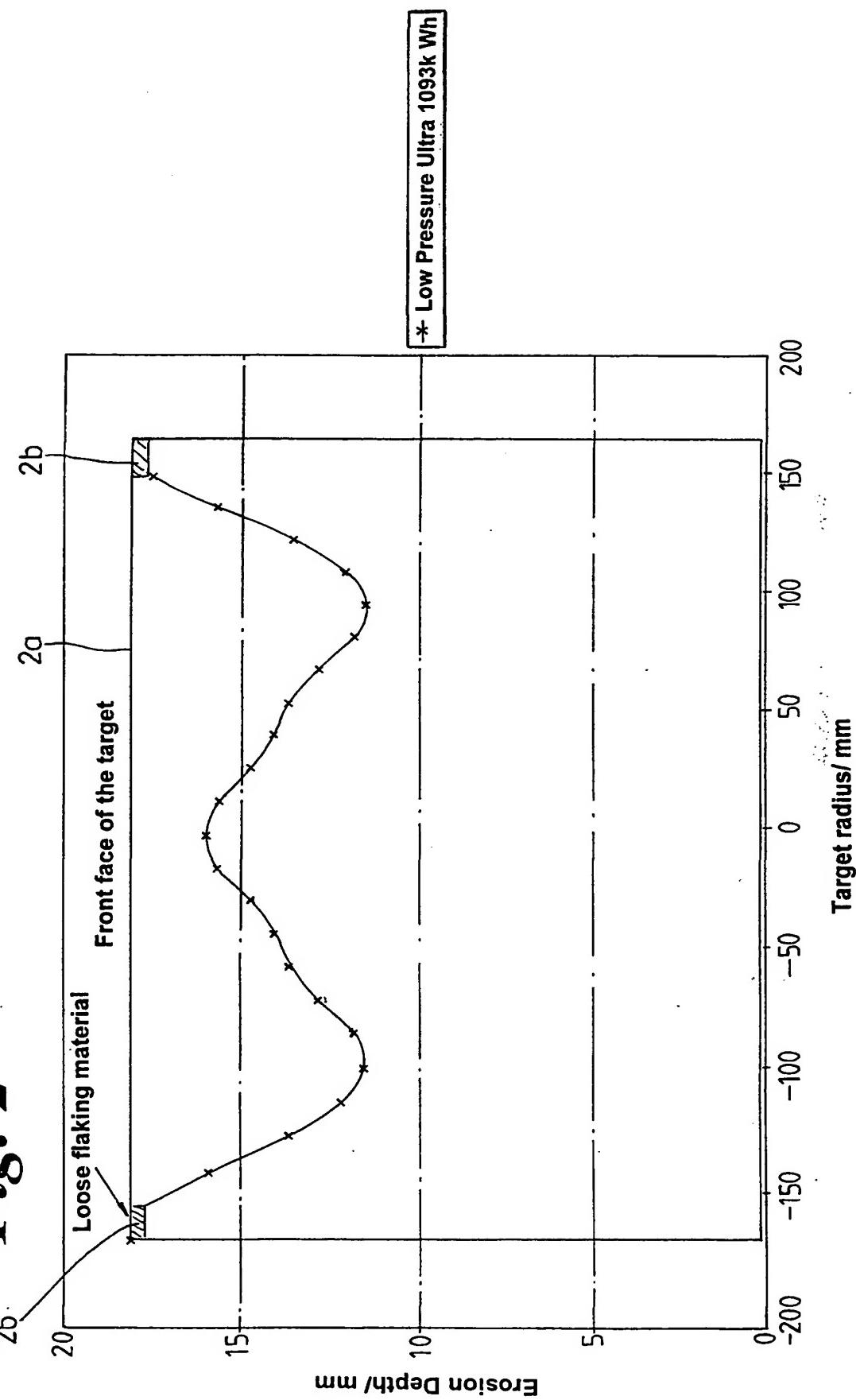


Fig. 1

SUBSTITUTE SHEET (RULE 26)

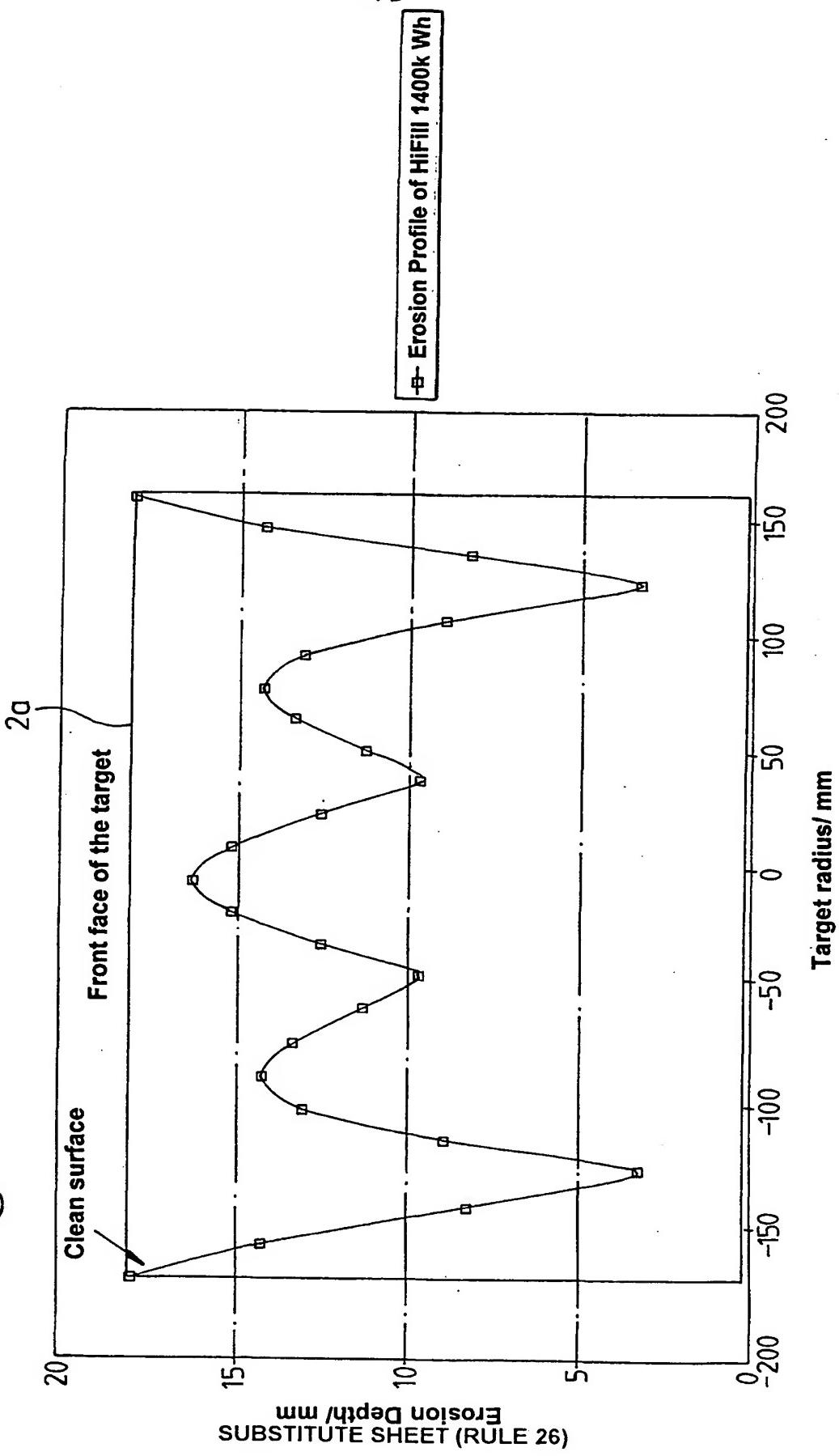
2/9

Fig. 2 Edge of target not eroded. Plasma confined by Secondary Magnetic Field



3/9

Fig. 3 Entire Target Surface eroded. No Secondary Magnetic Field



4/9

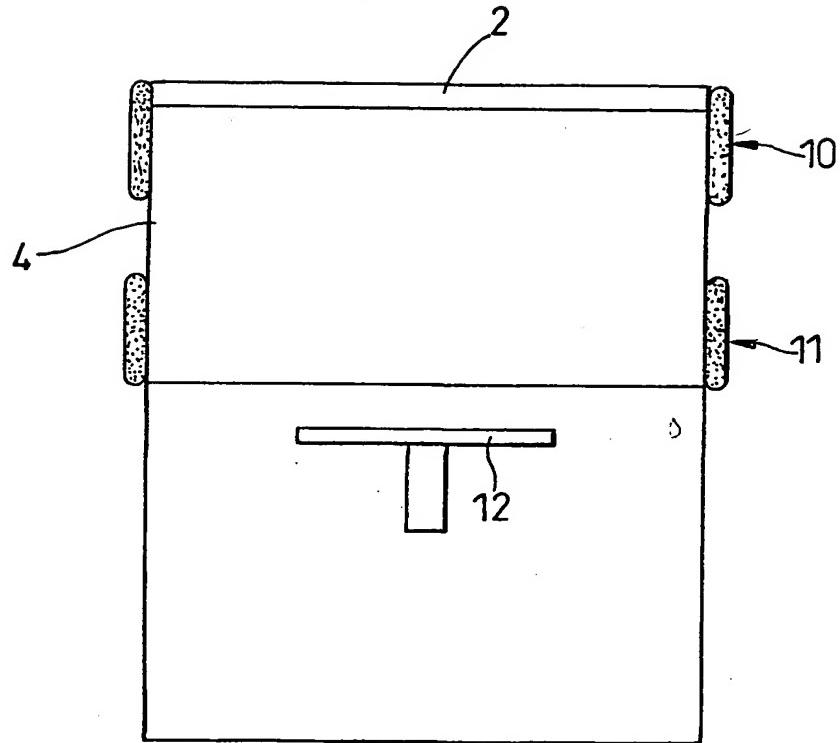


Fig. 4

SUBSTITUTE SHEET (RULE 26)

5/9

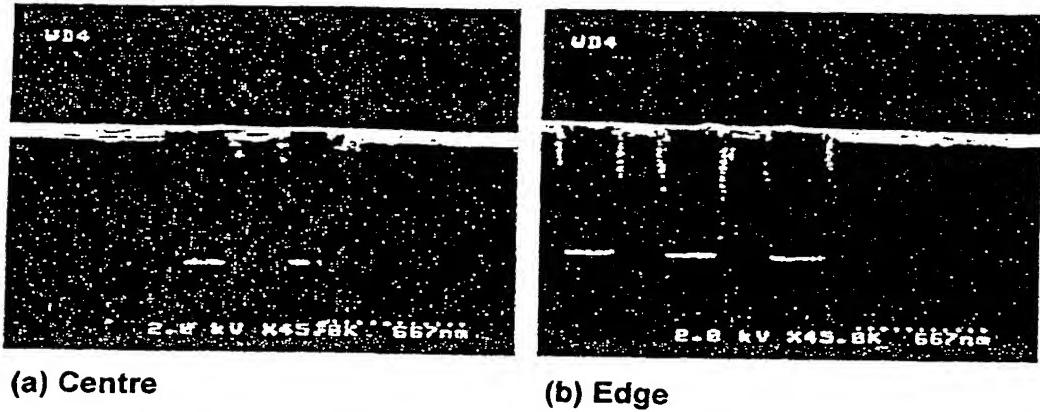
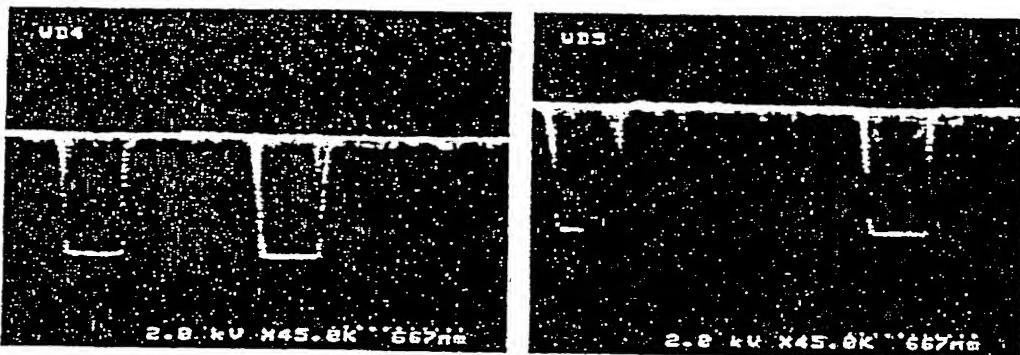
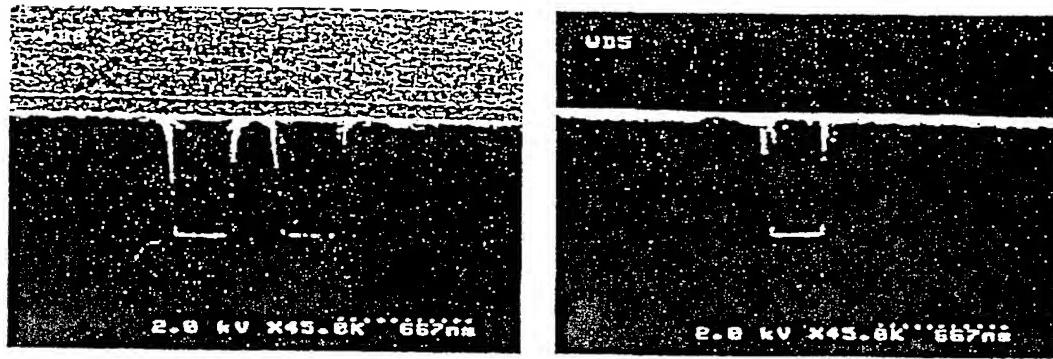


Fig. 5 (no coil power)



(a) Centre **(b) Edge**

Fig. 6 (target coil power only)

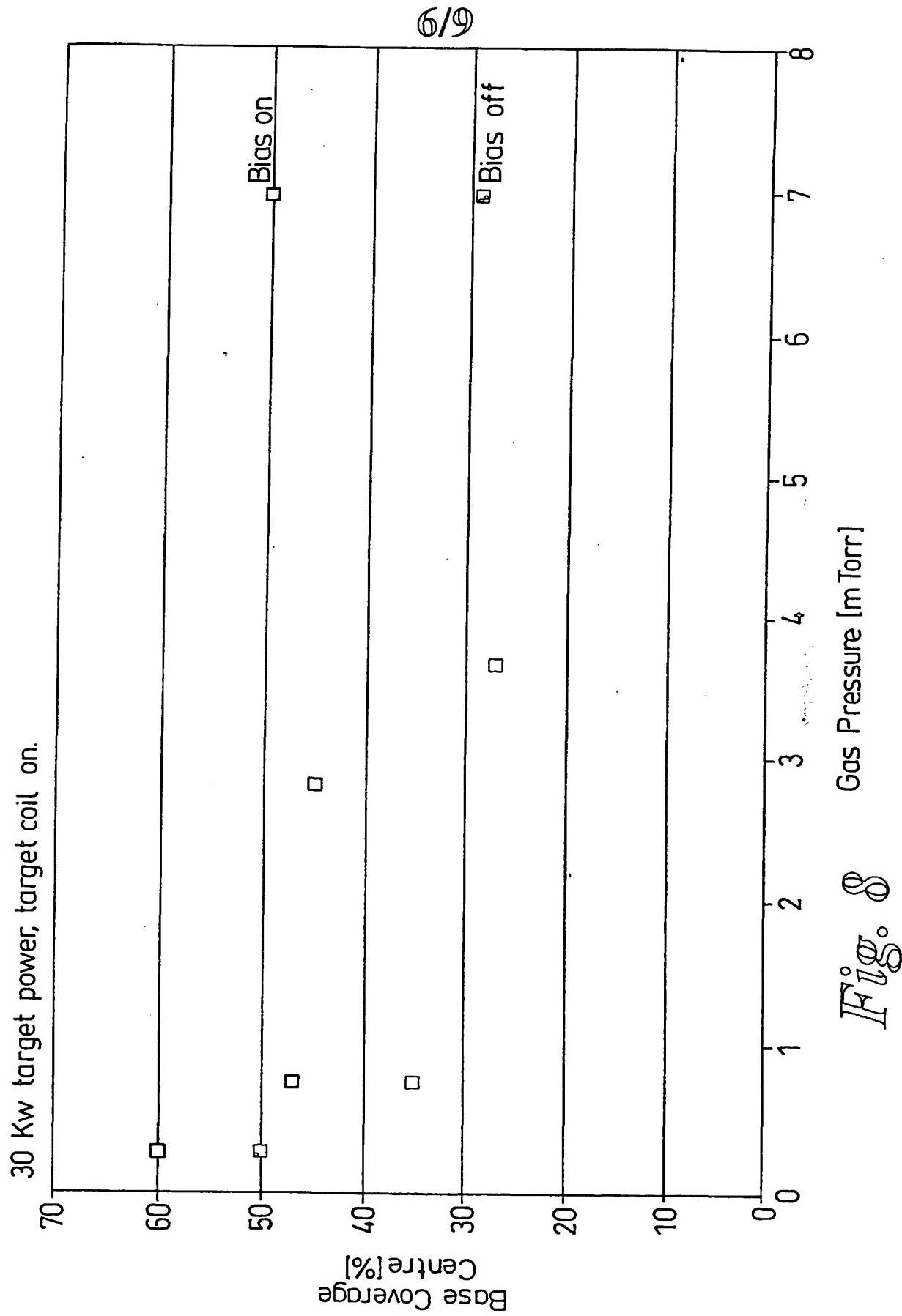


(a) Centre

(b) Edge

(target and coil power, coils energized to give the same magnetic pol to the centre, target coil in a 'buckling' i.e. magnetic polar opposition to the target magnetron) 

Fig. 7



SUBSTITUTE SHEET (RULE 26)

7/9

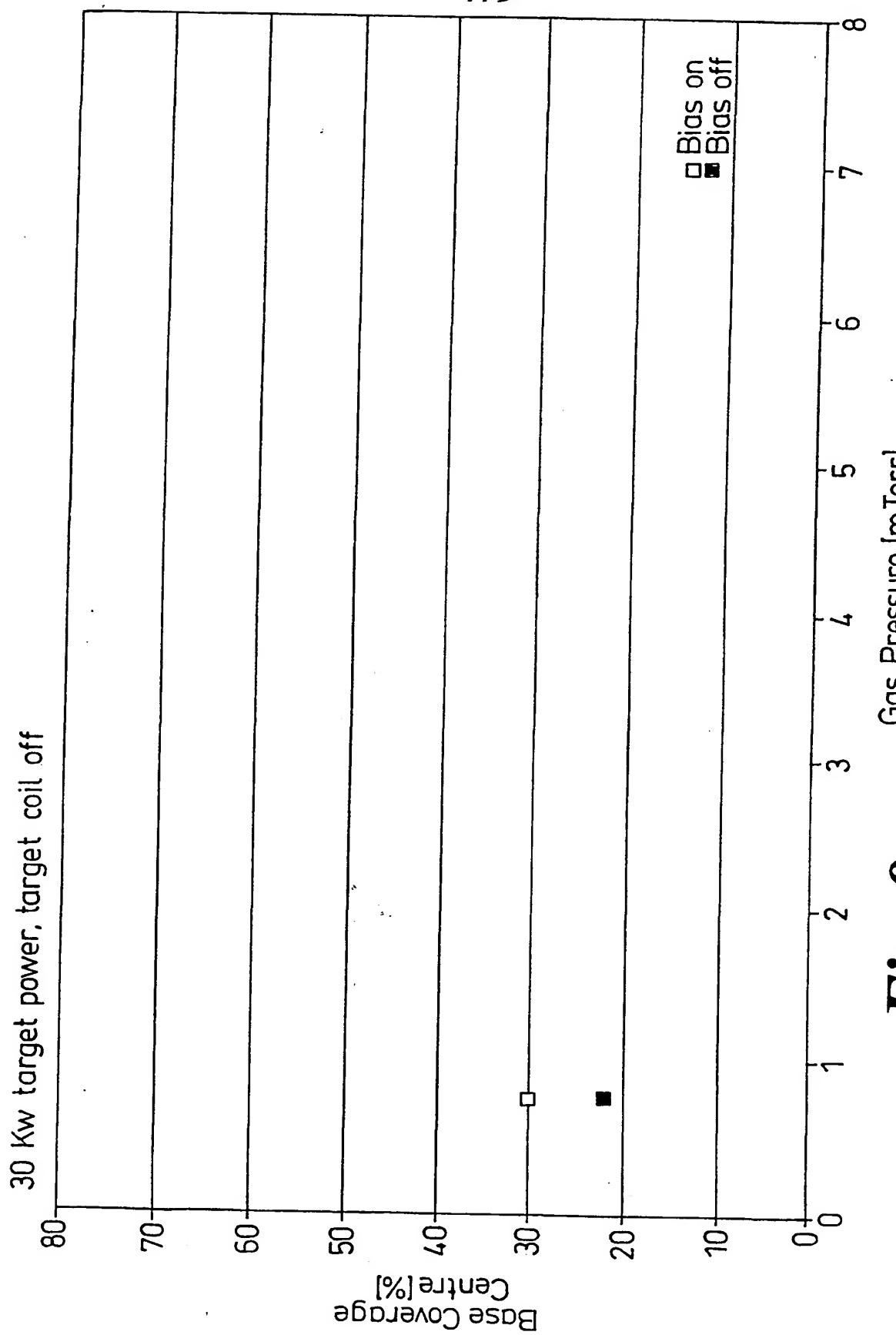
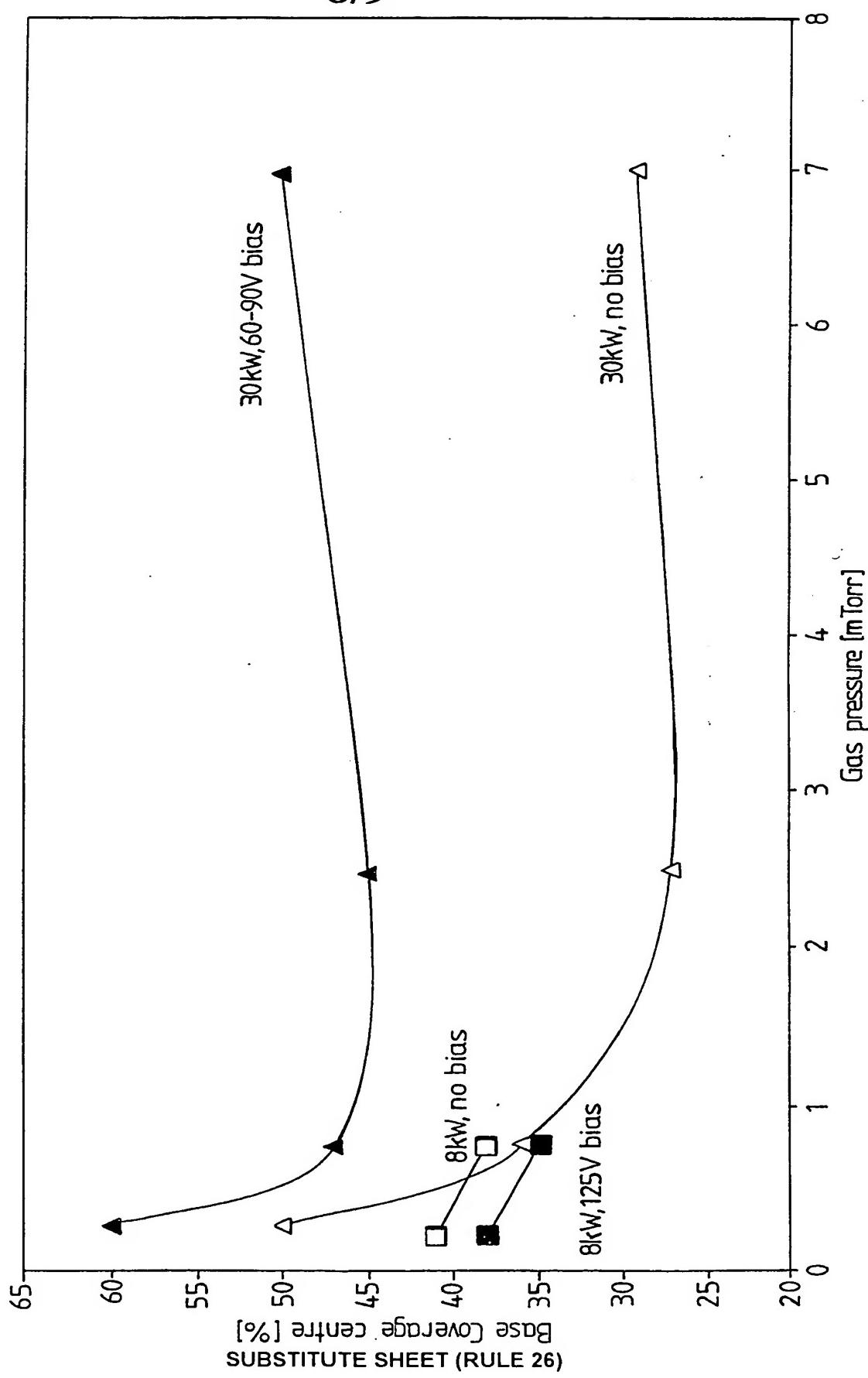
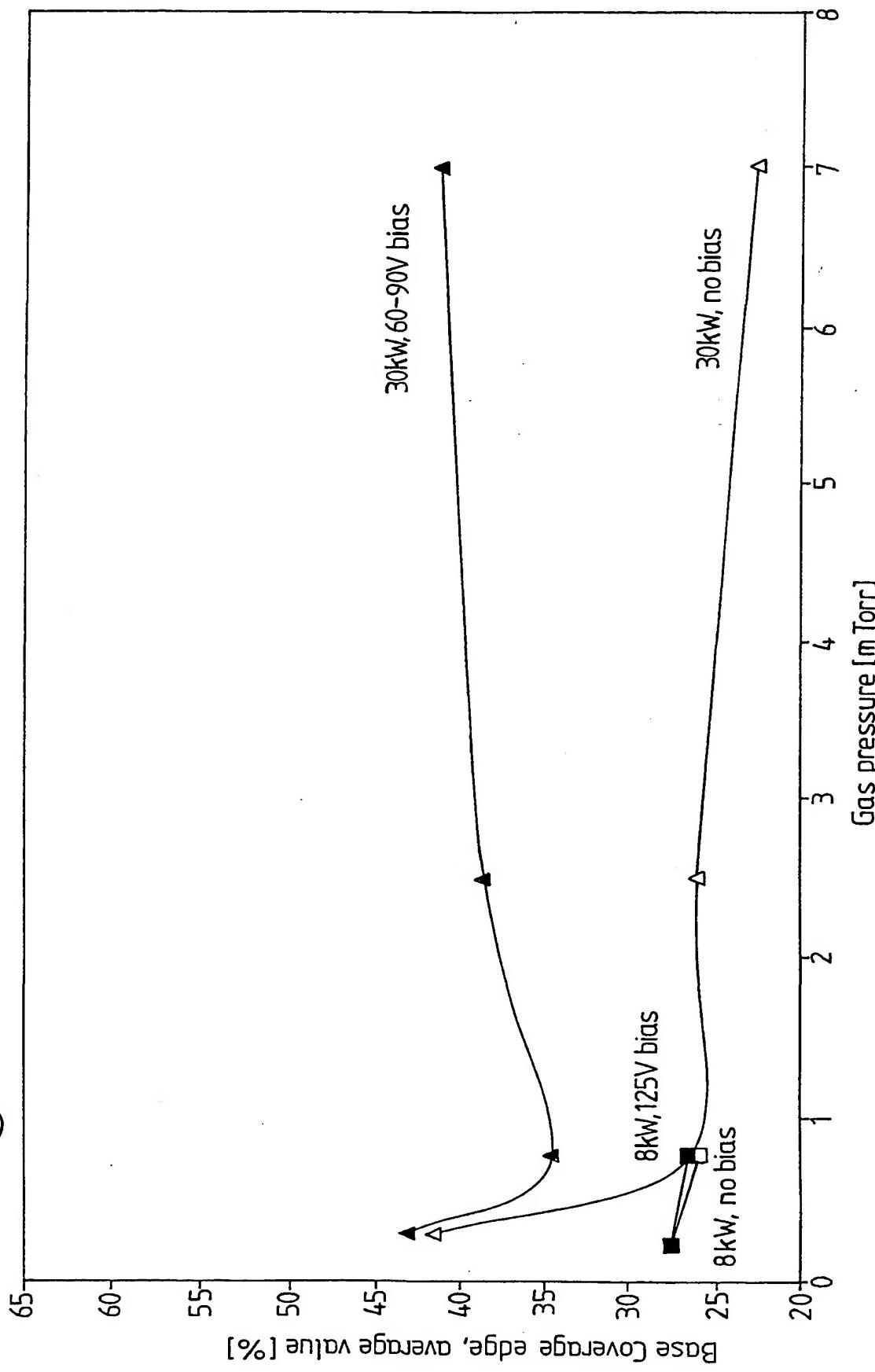


Fig 9

8/9

Fig. 10

9/9

Fig. 11

SUBSTITUTE SHEET (RULE 26)

INTERNATIONAL SEARCH REPORT

In tional Application No

PCT/GB 01/03229

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01J37/34

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 H01J C23C

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 182 001 A (FRITSCH WOLF E ET AL) 26 January 1993 (1993-01-26) column 3, line 5 - line 32 column 4, line 23 - line 44 column 5, line 57 -column 6, line 11 column 8, line 49 - line 59 figures 1-3	1,6,7
Y	---	2,4,5
X	PATENT ABSTRACTS OF JAPAN vol. 004, no. 065 (C-010), 16 May 1980 (1980-05-16) & JP 55 031142 A (HATA TOMONOBU), 5 March 1980 (1980-03-05) abstract; figures ---	1,6-8
	-/-	

 Further documents are listed in the continuation of box C. Patent family members are listed in annex.

° Special categories of cited documents :

- *A* document defining the general state of the art which is not considered to be of particular relevance
- *E* earlier document but published on or after the international filing date
- *L* document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)
- *O* document referring to an oral disclosure, use, exhibition or other means
- *P* document published prior to the international filing date but later than the priority date claimed

- *T* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
- *X* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
- *Y* document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.
- *&* document member of the same patent family

Date of the actual completion of the international search

15 November 2001

Date of mailing of the international search report

22/11/2001

Name and mailing address of the ISA

European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040, Tx. 31 651 epo nl,
Fax: (+31-70) 340-3016

Authorized officer

Aguilar, M.

INTERNATIONAL SEARCH REPORT

In ional Application No

PCT/GB 01/03229

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	GB 2 342 927 A (TRIKON HOLDINGS LTD) 26 April 2000 (2000-04-26) page 3, line 9 -page 5, line 26 page 9, line 16 - line 21 figures 15,16 -----	12,14,16
Y	---	2,4,5
A	US 5 772 858 A (TEPMAN AVI) 30 June 1998 (1998-06-30) column 3, line 20 -column 4, line 63 figure 3 -----	9

INTERNATIONAL SEARCH REPORT
Information on patent family members

In. International Application No

PCT/GB 01/03229

Patent document cited in search report	Publication date	Patent family member(s)			Publication date
US 5182001	A 26-01-1993	DE DE EP ES JP KR US	4018914 C1 59104022 D1 0461525 A1 2066270 T3 4254580 A 224507 B1 5069772 A	C1 D1 A1 T3 A B1 A	06-06-1991 09-02-1995 18-12-1991 01-03-1995 09-09-1992 15-10-1999 03-12-1991
JP 55031142	A 05-03-1980		NONE		
GB 2342927	A 26-04-2000	DE JP US	19950381 A1 2000129439 A 6179974 B1	A1 A B1	04-05-2000 09-05-2000 30-01-2001
US 5772858	A 30-06-1998		NONE		

